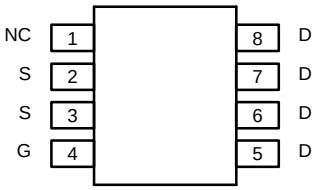
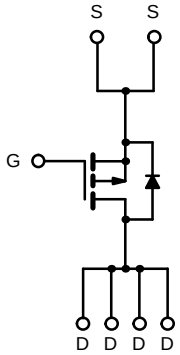
P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
–20	0.25 @ V_{GS} = –10 V	±2.5
	0.40 @ V_{GS} = –4.5 V	±2.0

SO-8



Top View



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	–20	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current (T_J = 150°C)[a]	T_A = 25°C	I_D	±2.5	A
	T_A = 70°C		±2.0	
Pulsed Drain Current		I_{DM}	±10	
Continuous Source Current (Diode Conduction)[a]		I_S	–2.0	
Maximum Power Dissipation[a]	T_A = 25°C	P_D	2.5	W
	T_A = 70°C		1.6	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 150	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient[a]	R_{thJA}	50	°C/W

Notes
a. Surface Mounted on FR4 Board, t ≤ 10 sec.

For SPICE model information via the Worldwide Web: http://www.vishay.com/www/product/spice.htm

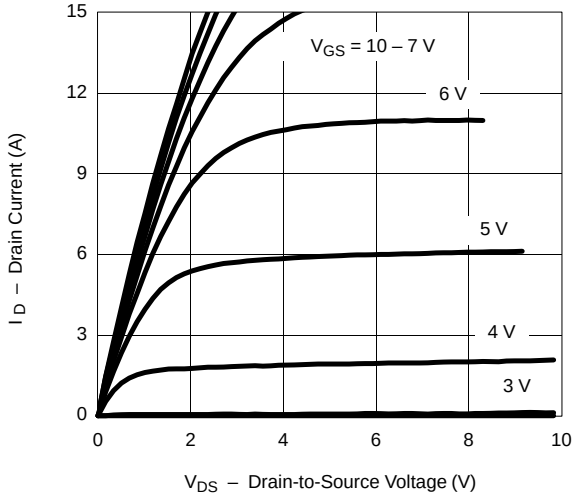
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ[a]	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = –250 μA	–1.0			V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = –16 V, V_{GS} = 0 V			–2	μA
		V_{DS} = –16 V, V_{GS} = 0 V, T_J = 55°C			–25	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} ≤ –5 V, V_{GS} = –10 V	–10			A
Drain-Source On-State Resistance[b]	$r_{DS(on)}$	V_{GS} = –10 V, I_D = 1 A		0.13	0.25	Ω
		V_{GS} = –4.5 V, I_D = 0.5 A		0.22	0.40	
Forward Transconductance[b]	g_{fs}	V_{DS} = –15 V, I_D = –2.5 A		2.5		S
Diode Forward Voltage[b]	V_{SD}	I_S = –1.25 A, V_{GS} = 0 V		–0.8	–1.6	V
Dynamic[a]						
Total Gate Charge	Q_g	V_{DS} = –10 V, V_{GS} = –10 V, I_D = –2.0 A		6.8	25	nC
Gate-Source Charge	Q_{gs}			1.3		
Gate-Drain Charge	Q_{gd}			1.6		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = –10 V, R_L = 10 Ω I_D ≅ –1 A, V_{GEN} = –10 V, R_G = 6 Ω		10	40	ns
Rise Time	t_r			12	40	
Turn-Off Delay Time	$t_{d(off)}$			20	90	
Fall Time	t_f			10	50	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 2 A, di/dt = 100 A/μs		69	100	

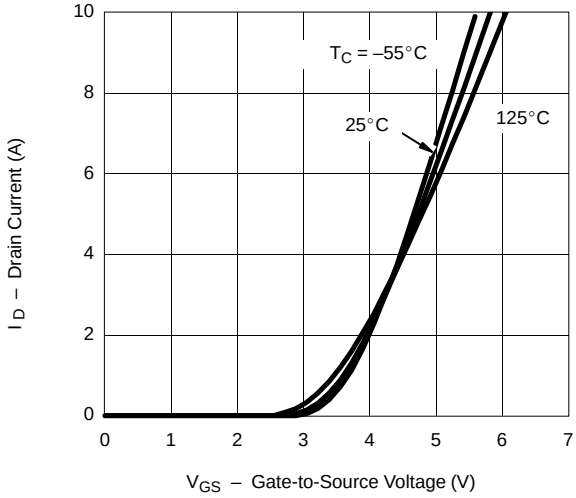
Notes
a. For design aid only; not subject to production testing.
b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

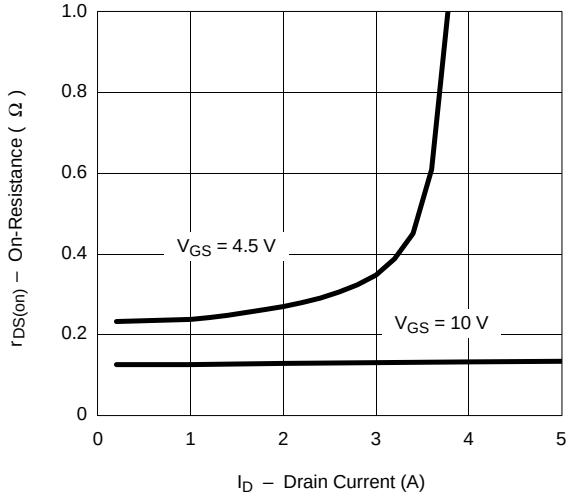
Output Characteristics



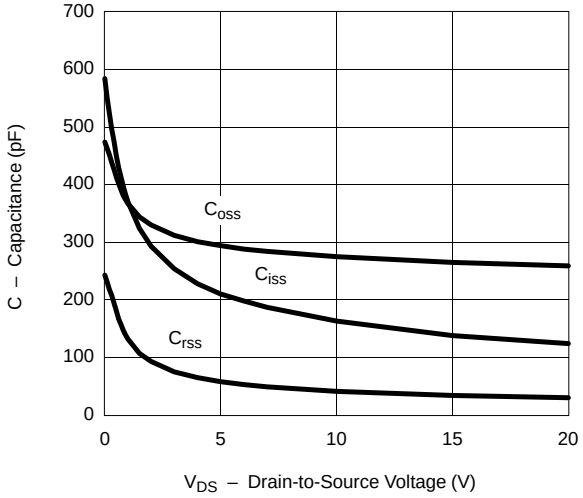
Transfer Characteristics



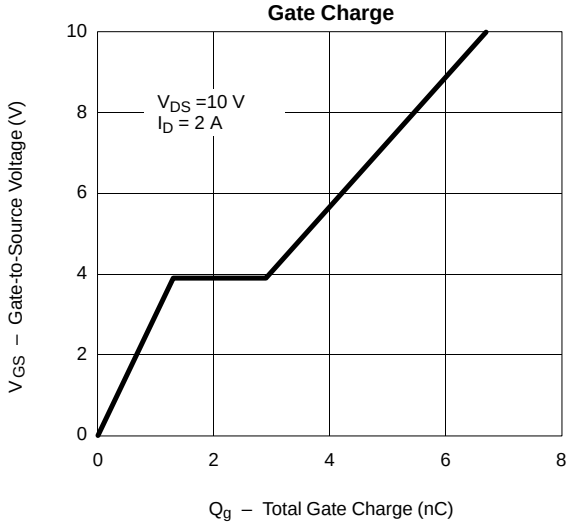
On-Resistance vs. Drain Current



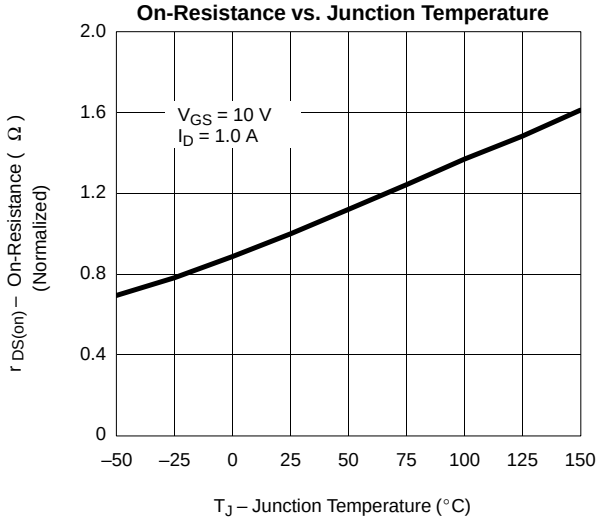
Capacitance



Gate Charge

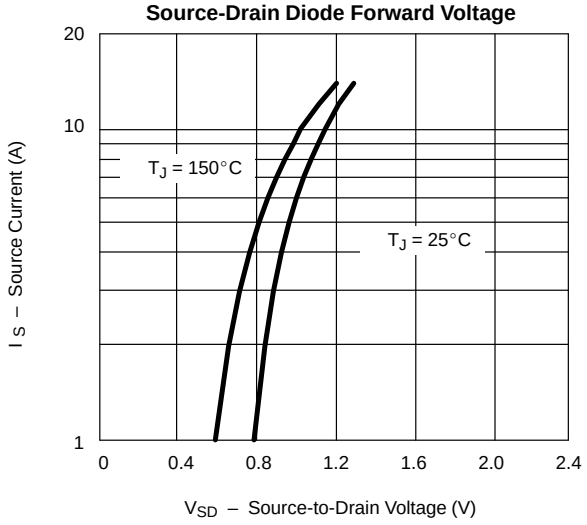


On-Resistance vs. Junction Temperature

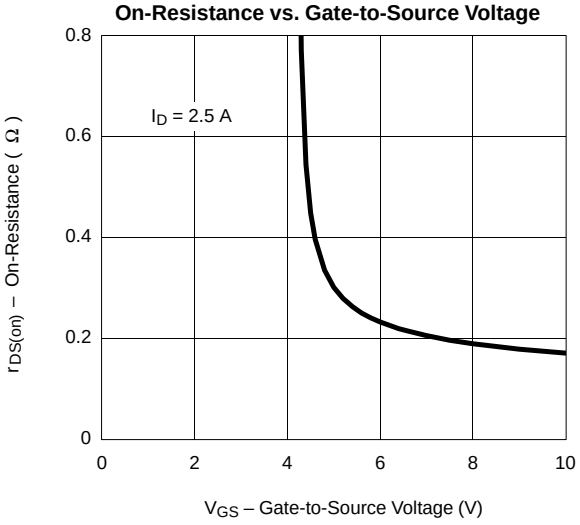


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

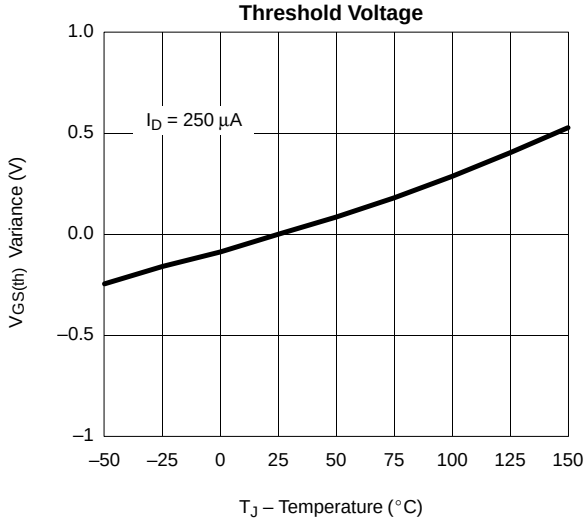
Source-Drain Diode Forward Voltage



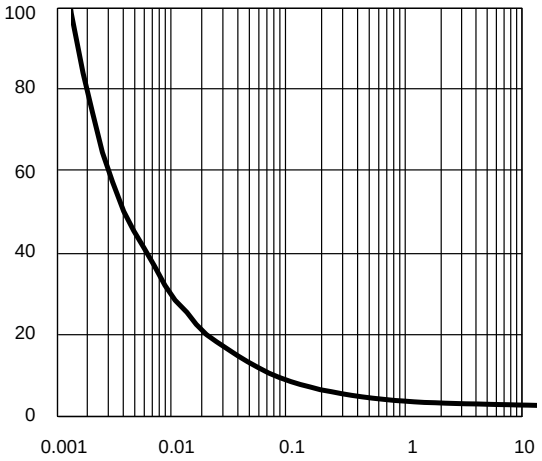
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient

